

Total No. of Questions : 8]

SEAT No. :

P2577

[Total No. of Pages : 2

M.E. (Semester - I)
VLSI AND EMBEDDED SYSTEMS
Analog and Digital CMOS IC Design
(2008 Pattern)

Time : 3 Hours]

[Max. Marks : 100

Instructions to the candidates:

- 1) *Answers to the two sections should be written in separate answer book.*
- 2) *Answer any three questions from each section.*
- 3) *Neat diagrams must be drawn wherever necessary.*
- 4) *Figures to the right side indicate full marks.*
- 5) *Use of Calculator is allowed.*
- 6) *Assume Suitable data if necessary.*

SECTION - I

- Q1)** a) What is need of voltage reference? Explain any one type of such reference circuit in detail ? **[8]**
- b) What are merits of cascode arrangement? Design cascode current source for 100 μ A. Assume suitable data. **[8]**
- Q2)** a) Carry out small signal analysis of differential amplifier. Derive the equation for CMRR. **[8]**
- b) What is need of low noise opamp? What are techniques to design? **[8]**
- Q3)** Draw FSM diagram for 10110 Mealy sequence detector, write VHDL code and test bench for it. **[16]**
- Q4)** Write short notes on **any three**. **[18]**
- a) MOSFET as diode
 - b) Inverters
 - c) Buffered opamp
 - d) High speed opamp

P.T.O.

SECTION - II

- Q5)** a) What is concept of metastability? How to sync up? What are solutions? [8]
b) What is need of technology scaling? What are types? Explain any one in brief. [8]
- Q6)** a) Design CMOS logic for $Y = ABC + DEFGH$. Compute active area on chip. [8]
b) Derive the expressions for static, dynamic power dissipations and power delay product. [8]
- Q7)** a) Design latch using transmission gates. [8]
b) Draw top view showing metal/poly Silicon layout routing for 2 input CMOS NAND gate. Show the dimensions. [8]
- Q8)** Write short notes on **any three**. [18]
a) DRC rules
b) Advanced trends for ultra fast logic
c) Transient response
d) NORA logic

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